

200V P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET IN SOT23

Features and Benefits

- $V_{(BR)DSS} > -200V$
- $R_{DS(on)} \le 80\Omega$ @ $V_{GS} = -10V$
- Maximum continuous drain current I_D = -35mA
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

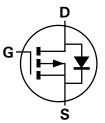
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)

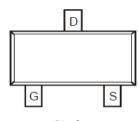




Top View



Device symbol



Pin-Out Top View

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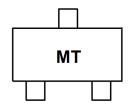
Ordering Information (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVP1320FTA	MT	7	8	3000

Notes:

- No purposefully added lead
 Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

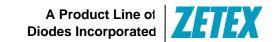
Marking Information



MT = Product Type Marking Code

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Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-200	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current	I _D	-35	mA
Pulsed Drain Current (Note 5)	I _{DM}	-400	mA

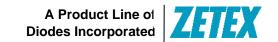
Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 4)	P _D	350	mW
Thermal Resistance, Junction to Ambient	(Note 4)	R _{0JA}	357	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

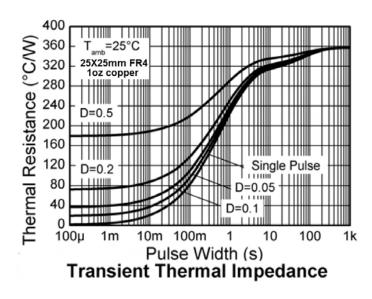
Notes:

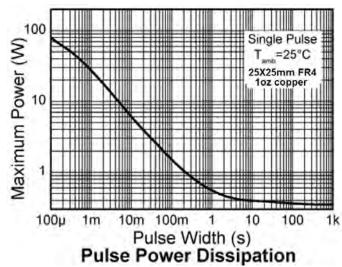
- 4. For a device mounted on 25mm X 25mm X 1.6mm FR-4 PCV with high coverage of single sided 1oz copper, in still air condition.
- 5. Device mounted on minimum recommended pad layout test board, 10μ s pulse duty cycle = 1%.

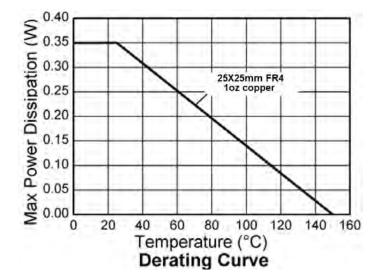




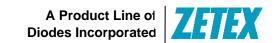
Thermal Characteristics











Electrical Characteristics @TA = 25°C unless otherwise specified

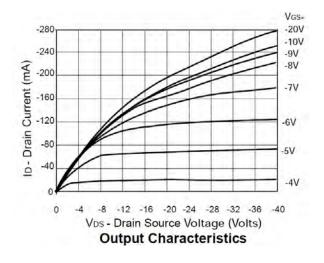
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	-200	-	1	V	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-1 -20	μA	V _{DS} = -200V, V _{GS} = 0V V _{DS} = -160V, V _{GS} = 0V, T _A = 125°C	
Gate-Source Leakage	I _{GSS}	-	-	±20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
On-State Drain Current	I _{D(on)}	-100	-	-	mA	$V_{GS} = -10V, V_{DS} = -15V$	
ON CHARACTERISTICS (Note 6)			-				
Gate Threshold Voltage	V _{GS(th)}	-1.5	-	-3.5	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Static Drain-Source On-Resistance	R _{DS (on)}	-	-	80	Ω	$V_{GS} = -10V, I_D = -50mA$	
Forward Transconductance	9 fs	25	-	-	mS	$V_{DS} = -15V, I_{D} = -50mA$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	-	-	50	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	-	15	pF		
Reverse Transfer Capacitance	C _{rss}	-	-	5	pF		
Turn-On Delay Time	t _{D(on)}	-	-	8	ns	V _{DS} = -25V, I _D = -50mA	
Turn-On Rise Time	t _r	-	-	8	ns		
Turn-Off Delay Time	t _{D(off)}	-	-	8	ns		
Turn-Off Fall Time	tf	-	-	16	ns		

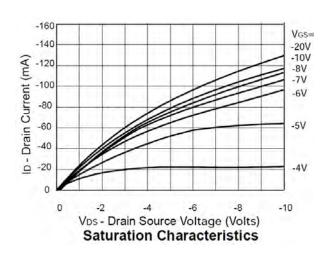
Notes: 6. Short duration pulse test used to minimize self-heating effect.

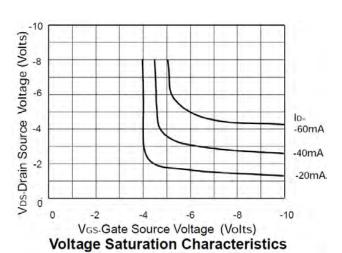
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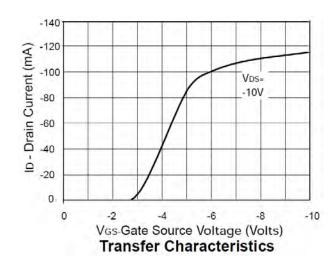


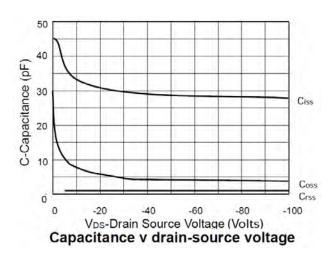
Electrical Characteristics

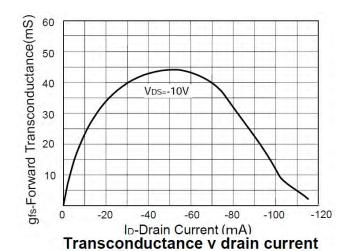






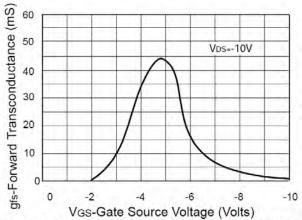




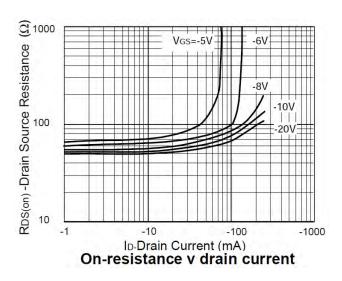


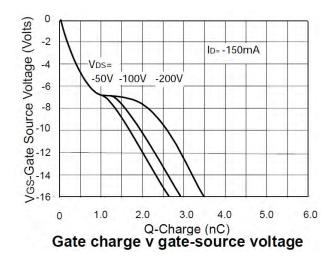


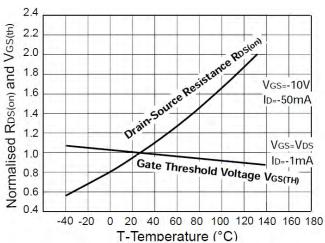
Electrical Characteristics (cont.)



Transconductance v gate-source voltage



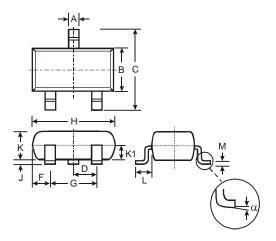




Normalised RDS(on) and VGS(th) vs Temperature

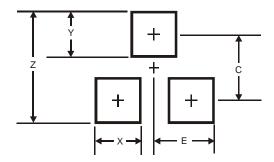


Package Outline Dimensions



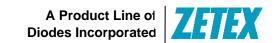
SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35





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